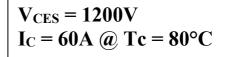
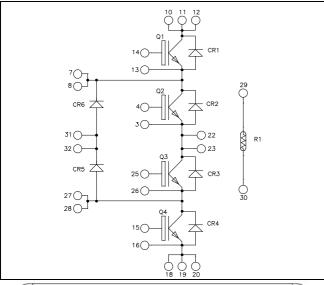
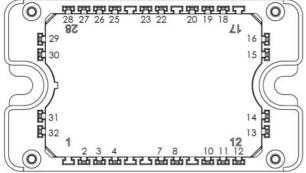


## Three level inverter Trench + Field Stop IGBT4







All multiple inputs and outputs must be shorted together Example: 10/11/12; 7/8 ...

#### Application

- Solar converter
- Uninterruptible Power Supplies

#### **Features**

- Trench + Field Stop IGBT 4
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

### All ratings @ $T_i = 25$ °C unless otherwise specified

#### Q1 to Q4 Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage		1200	V
Τ	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
$I_{\rm C}$	Continuous Collector Current $T_C = 8$		60	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Power Dissipation	$T_C = 25$ °C	280	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

### Q1 to Q4 Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ , $V_{CE} =$			1	mA	
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V
		$I_C = 50A$	$T_j = 150$ °C		2.2		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1.6 \text{mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

### Q1 to Q4 Dynamic Characteristics (per IGBT)

_	Characteristic	Test Conditions	r	Min	Typ	Max	Unit
Cies	Input Capacitance	$\begin{aligned} V_{GE} &= 0V \\ V_{CE} &= 25V \end{aligned}$			2770		
$C_{oes}$	Output Capacitance				205		pF
Cres	Reverse Transfer Capacitance	f = 1MHz			160		
$Q_{\mathrm{G}}$	Gate charge	$V_{GE} = \pm 15V ; V_{C} = 100$		0.38		μС	
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			50		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			27		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 50A$			270		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 8.2\Omega$		70			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 50A$ $R_{G} = 8.2\Omega$			50		
$T_{r}$	Rise Time				30		ns
T <sub>d(off)</sub>	Turn-off Delay Time				290		115
$T_{\rm f}$	Fall Time				80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25$ °C		3.8		mJ
Lon	Turn-on Switching Energy	$V_{CE} = 600V$	$T_J = 150$ °C		5.5		1113
$E_{\rm off}$	Turn-off Switching Energy	$I_C = 50A$	$T_J = 25^{\circ}C$		2.5		mJ
2011	Turn on Switching Directly	$R_G = 8.2\Omega$	$T_J = 150$ °C		4.5		1110
$I_{sc}$	Short Circuit data	$ \begin{array}{l} V_{GE} \! \leq \! \! 15V \; ; V_{Bus} \! = \! 900V \\ t_{p} \! \leq \! \! 10\mu s \; ; T_{j} \! = \! 150^{\circ} C \end{array} $			200		A
$R_{thJC}$	Junction to Case Thermal Resistance					0.53	°C/W



# CR1 to CR6 diode ratings and characteristics (per diode) Symbol Characteristic Test Conditions

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage					1200	V
$I_{RM}$	Reverse Leakage Current	$V_{R} = 600V$				100	μA
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		30		A
		$I_F = 30A$			2.6	3.1	
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 60A$			3.2		V
		$I_F = 30A$	$T_j = 125$ °C		1.8		V
,	Reverse Recovery Time  Reverse Recovery Charge		$T_j = 25$ °C		300		***
$t_{rr}$		$I_F = 30A$	$T_j = 125$ °C		380		ns
0		$\begin{array}{c} \hline V_R = 800V \\ di/dt = 200A/\mu s \end{array}$	$T_j = 25$ °C		360		пC
$Q_{rr}$			$T_j = 125$ °C		1700		пС
E <sub>rr</sub>	Reverse Recovery Energy	$\begin{split} I_F = 30A \\ V_R = 800V \\ di/dt = 1000A/\mu s \end{split}$	$T_j = 125$ °C		1.6		mJ
$R_{\text{thJC}}$	Junction to Case Thermal Resistance					1.2	°C/W

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$			5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$		3952		K
$\Delta B/B$	$T_{\rm C}$ =100°C		4		%

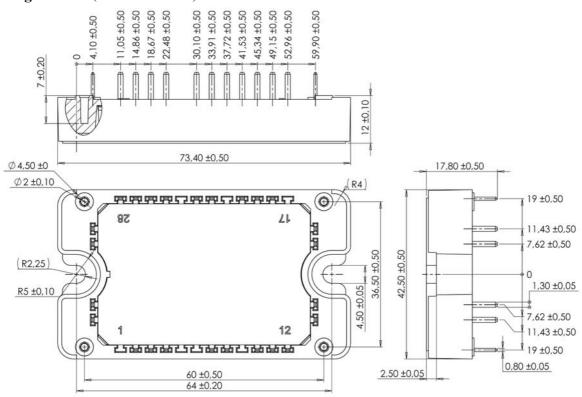
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

### Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case	4000		V		
$T_{J}$	Operating junction temperature range	-40	175			
$T_{JOP}$	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
$T_{STG}$	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

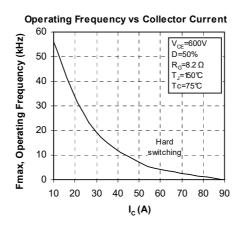


#### Package outline (dimensions in mm)

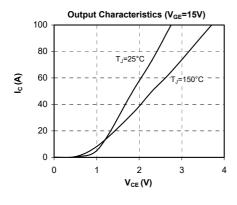


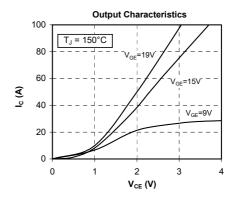
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

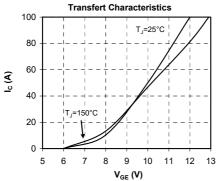
### Q1 to Q4 Typical performance curve

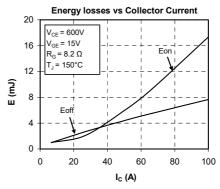


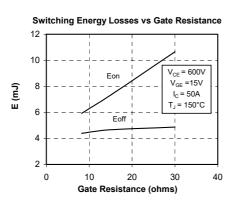


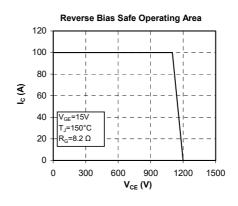


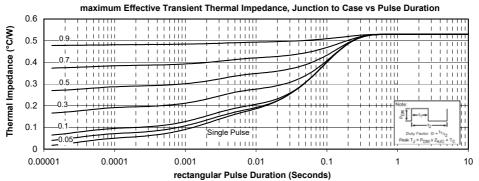






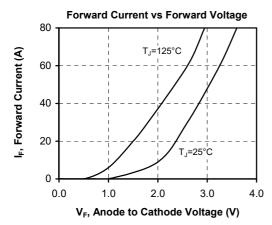




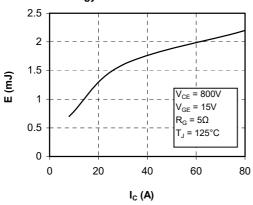




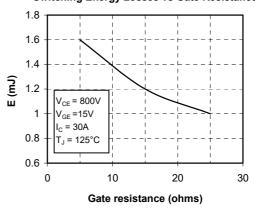
### CR1 to CR6 Typical performance curve



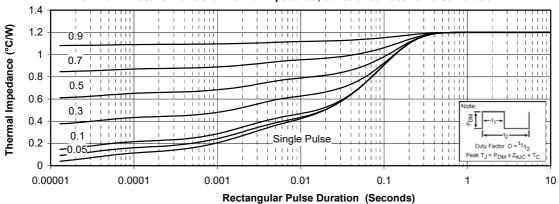
#### **Energy losses vs Collector Current**



#### **Switching Energy Losses vs Gate Resistance**









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